

Descriptions

- Switching application
- Interface circuit and driver circuit application

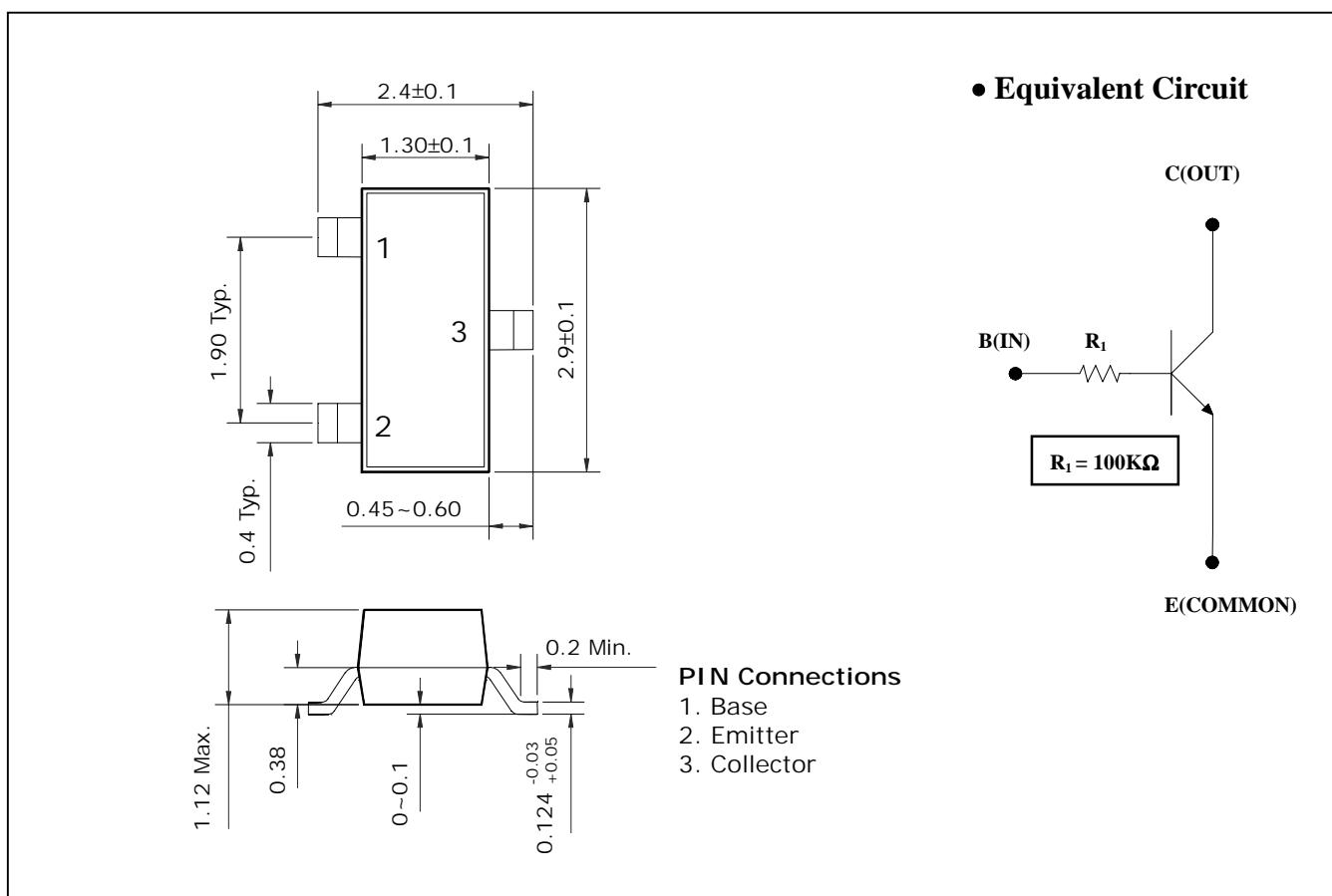
Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

Ordering Information

| Type NO. | Marking | Package Code |
|----------|---------|--------------|
| SRC1212S | RCB | SOT-23 |

Outline Dimensions

unit : mm


Absolute maximum ratings

(Ta=25°C)

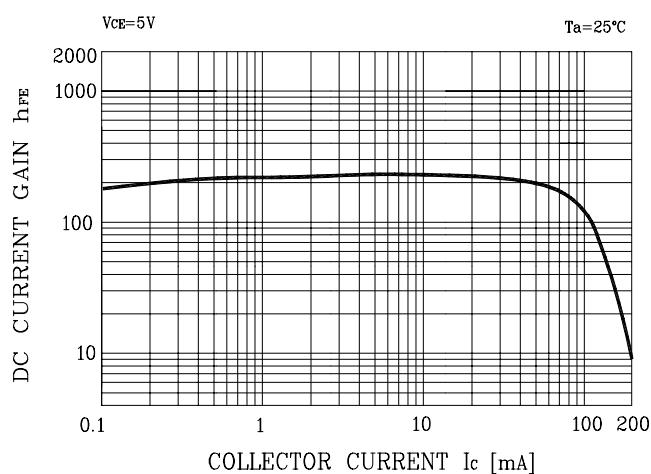
| Characteristic | Symbol | Ratings | Unit |
|---------------------------|------------------|-----------|------|
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 50 | V |
| Emitter-Base Voltage | V _{EBO} | 5 | V |
| Collector Current | I _C | 100 | mA |
| Power Dissipation | P _D | 200 | mW |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55 ~ 150 | °C |

Electrical Characteristics

(Ta=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------------------|-----------------------------|---|------|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} =50V, I _E =0 | - | - | 500 | nA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} =5V, I _C =0 | - | - | 500 | nA |
| DC Current Gain | h _{FE} | V _{CE} =5V, I _C =1mA | 120 | - | - | - |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | I _C =10mA, I _B =0.5mA | - | 0.1 | 0.3 | V |
| Transition Frequency | f _T [*] | V _{CE} =10V, I _C =5mA | - | 250 | - | MHz |
| Input Resistance | R _I | - | - | 100 | - | KΩ |

*: Characteristic of Transistor Only

Electrical Characteristic Curves**Fig. 1 h_{FE} - I_C****Fig. 2 V_{CE(SAT)} - I_C**